



IXFK20N120P Information

www.helsener.com

For Reference Only

Part Number IXFK20N120P

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1200V 20A TO-264

Package TO-264-3, TO-264AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IXFK20N120P Specifications

Manufacturer Part Number IXFK20N120P Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-264-3, TO-264AA Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ ImA Gate Charge (Qg) (Max) @ Vgs 193nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 11100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 780W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264A3, TO-264AA		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-264-3, TO-264AA Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ ImA Gate Charge (Qg) (Max) @ Vgs 193nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 11100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 780W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264AA, TO-264AA	Manufacturer Part Number	IXFK20N120P
Package TO-264-3, TO-264AA Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 193nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 11100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 780W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264AA	Manufacturer	IXYS
Package TO-264-3, TO-264AA Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 193nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 11100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 780W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264AA	Category	Discrete Semiconductor Products
Series HiPerFET?, PolarP2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 193nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 11100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 780W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature 55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 70-264AA (IXFK) Package / Case		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 193nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 11100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 780W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature 55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 70-264AA (IXFK) Package / Case	Package	TO-264-3, TO-264AA
Technology Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 20A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 193nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature - Supplier Device Package TO-264AA (IXFK) Package / Case MOSFET (Metal Oxide) 1200V MOSFET (Metal Oxide) 1200V 1200V 1200V 10V 10V 10V 11V 6.5V @ ImA 11100pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Series	HiPerFET?, PolarP2?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package TO-264AA (IXFK) Package / Case 20A (Tc) 21A (ToV) 21A (ToV) 22A (Tc) 23A (Tc) 24A (TV) 25C (TJ) 26A (TV) 26A (TV)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 193nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature **Operating Temperature** Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case **To-264AA	Drain to Source Voltage (Vdss)	1200V
Vgs(th) (Max) @ Id 6.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 193nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 11100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 780W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Current - Continuous Drain (Id) @ 25°C	20A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 11100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 11100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 780W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Vgs(th) (Max) @ Id	6.5V @ 1mA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 780W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Gate Charge (Qg) (Max) @ Vgs	193nC @ 10V
FET Feature - Rower Dissipation (Max) 780W (Tc) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Input Capacitance (Ciss) (Max) @ Vds	11100pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 570 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs570 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-264AA (IXFK)Package / CaseTO-264-3, TO-264AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Power Dissipation (Max)	780W (Tc)
Mounting Type Through Hole Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Rds On (Max) @ Id, Vgs	570 mOhm @ 10A, 10V
Supplier Device Package TO-264AA (IXFK) Package / Case TO-264-3, TO-264AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-264-3, TO-264AA	Mounting Type	Through Hole
	Supplier Device Package	TO-264AA (IXFK)
Report errors?	Package / Case	TO-264-3, TO-264AA
		Report errors?

IXFK20N120P Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXFK20N120P Payment Methods



















IXFK20N120P Shipping Methods













If you have any question about IXFK20N120P, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com